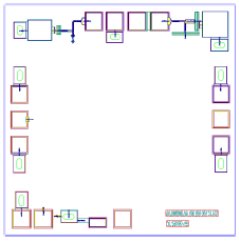
AMT1107
14 – 18GHz Power Amplifier Chip



Key Features :

- Frequency range : 14 – 18GHz
- Small signal gain : 19dB
- Saturated output power : 22.8dBm
- Voltage bias : 8V, 0.125A
- Chip dimensions : 1.8mm x 0.9mm x 0.1mm
- Applications : wireless communication, transceiver module, radio telecommunication etc.

Description :

AMT1107 chip is a Gallium Arsenide (GaAs) designed power amplifier chip, with a frequency range of 14 – 18GHz, single voltage operation, drain voltage Vds at 8V, linear gain of 19dB, saturated output power of 22.8dBm. This chip is designed with ground through metal vias on the back technology. All chip products p are 100% RF tested.

Absolute Maximum Ratings (Ta = 25°C)

Symbol	Parameter	Value	Remark
Vd	Drain Voltage	+11V	
Pin	Input Signal Power	15dBm	
Tch	Channel Operating Temperature	-55 ~ +125°C	
Tm	Junction Temperature	310°c	30s, N_2 protection
Tstg	Storage Temperature	-65 ~ +150°c	

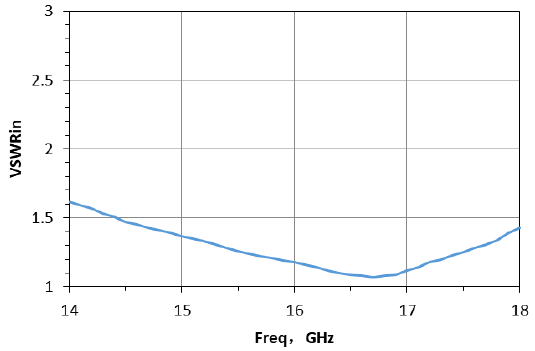
[1] Operation outside any of the Absolute Maximum Ratings may cause permanent device damage.

Electrical Characteristics (Ta = 25°C)

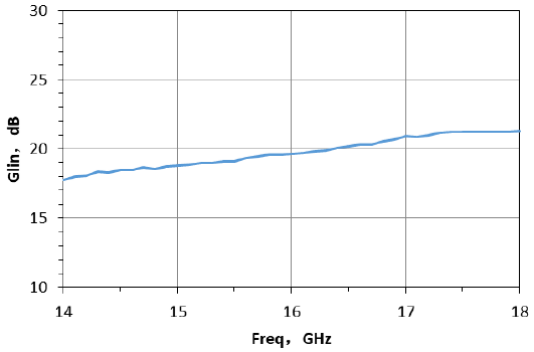
Symbol	Parameter	Test Condition	Value			Unit
			Min	Typical	Max	
G	Small Signal Gain	Vd = 8V F : 14 ~ 18GHz	17	19	21	dB
Id	Operating Current		-	125	-	mA
VSWR_in	Input SW		-	1.5	-	-
Gp	Power Gain	Vd = 8V F : 14 ~ 18GHz CW Operation		15	-	dB
Po(sat)	Saturated Output Power		-	22.8	-	dBm

Typical Performance

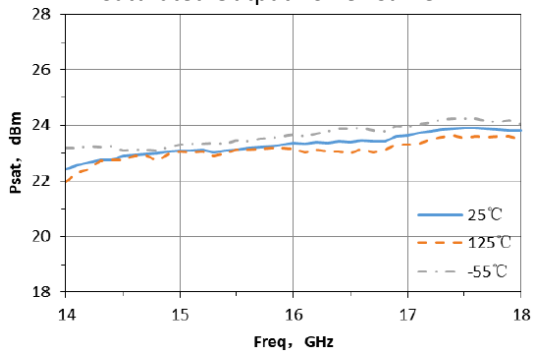
Input Standing Wave Curve



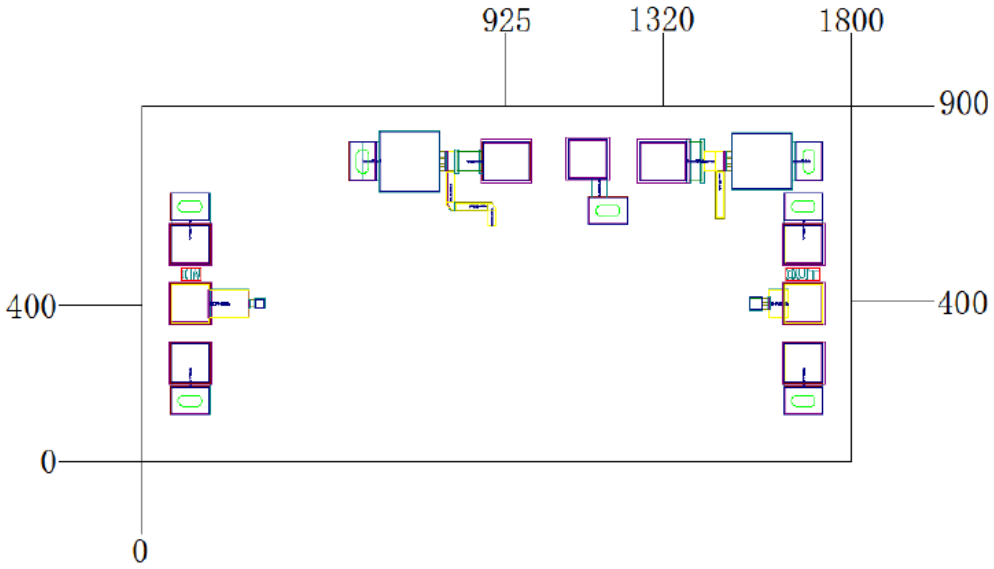
Linear Gain Curve



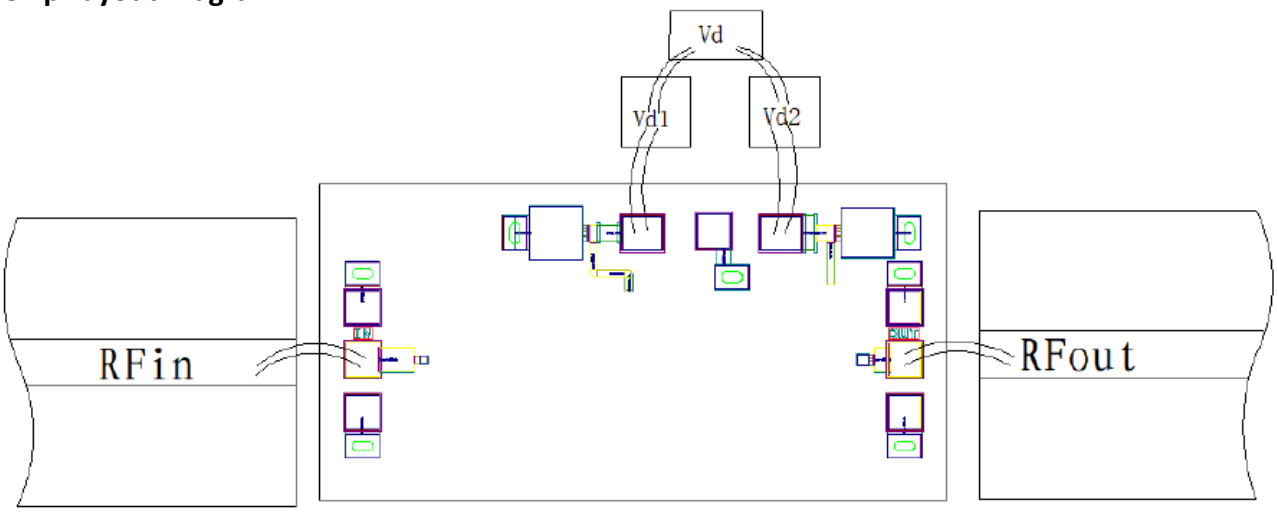
Saturated Output Power Curve



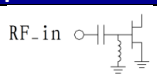
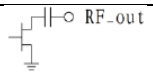
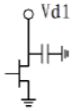
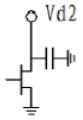
Chip Dimensions (Unit : μm)



Chip Layout Diagram



Pad Definition

Symbol	Function	Dimension	Equivalent Circuit
RF_in	RF signal input port, connecting to external 50Ω system. Built in internal DC blocking capacitor.	90*100μm^2	
RF_out	RF signal output port, connecting to external 50Ω system, Built in internal DC blocking capacitor.	90*100μm^2	
Vd1	Amplifier drain bias, need external 100pF, 1000pF capacitor.	100*100μm^2	
Vd2	Amplifier drain bias, need external 100pF, 1000pF capacitor.	106*100μm^2	

Please see Appendix A for details.